

ABSTRACT

The turn on time of an electrostatic discharge (ESD) structure, such as a silicon controlled rectifier (SCR), a low-voltage triggering SCR (LVTSCR), and a bipolar SCR (BSCR), is reduced by turning on the
5 structure in two steps: a first step that locally turns on the pnp and npn transistors, and a second step that, over time, fully turns on the structure.